

## N-Channel 20 V (D-S) MOSFET

### PRODUCT SUMMARY

$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ ) Max.	$I_D$ (A)	$Q_g$ (Typ.)
20	0.300 at $V_{GS} = 4.5$ V	0.9	3.5
	0.350 at $V_{GS} = 2.5$ V	0.7	

### FEATURES

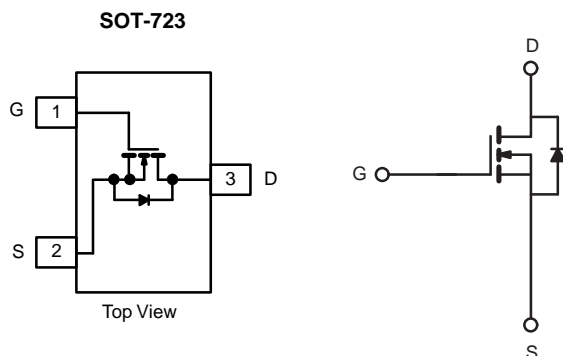
- Halogen-free According to IEC 61249-2-21 Definition
- Trench Power MOSFET
- 100 %  $R_g$  Tested
- Compliant to RoHS Directive 2002/95/EC



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Load Switching for Portable Devices
- DC/DC Converter



### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

Parameter	Symbol	5 s	Steady State	Unit
Drain-Source Voltage	$V_{DS}$	20		V
Gate-Source Voltage	$V_{GS}$	$\pm 12$		
Continuous Drain Current ( $T_J = 150^\circ\text{C}$ ) <sup>a</sup>	$I_D$	0.9	0.72	A
		0.68	0.57	
Pulsed Drain Current ( $t = 300 \mu\text{s}$ ) <sup>b</sup>	$I_{DM}$	3.5		
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	0.72	0.6	
Power Dissipation <sup>a</sup>	$P_D$	0.35	0.28	W
		0.21	0.16	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150		$^\circ\text{C}$

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	120	145	$^\circ\text{C/W}$
		140	175	
Maximum Junction-to-Foot	$R_{thJF}$	62	78	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. Pulse width limited by maximum junction temperature.

**SPECIFICATIONS** ( $T_A = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

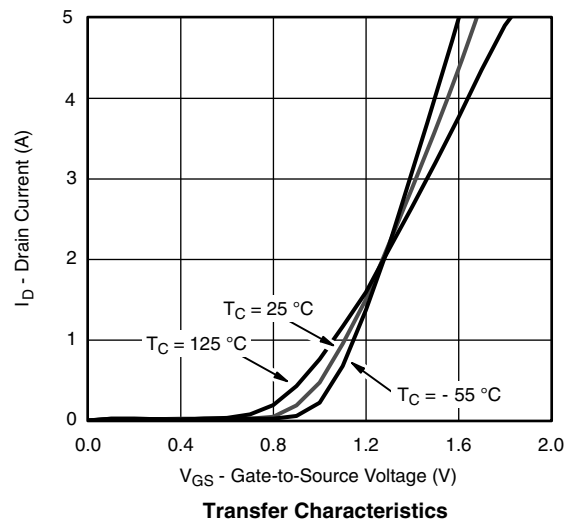
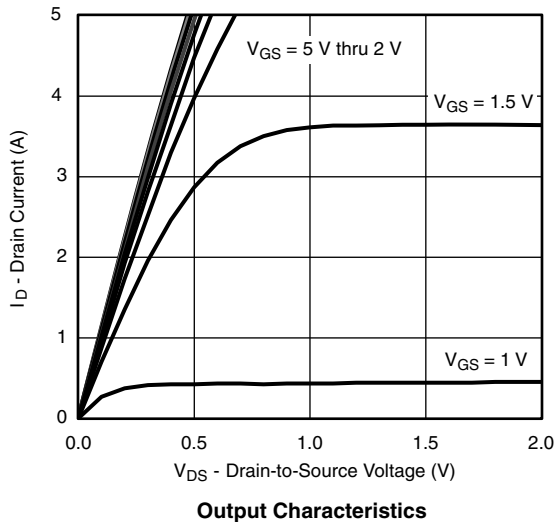
Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	20			V
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	0.50		0.90	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 8 V			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C			75	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 10 V, V <sub>GS</sub> = 4.5 V	6			A
Drain-Source On-Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 0.9A		0.300		Ω
		V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 0.7 A		0.350		
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 0.9 A		13		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 0.95 A, V <sub>GS</sub> = 0 V		0.7	1.2	V
Dynamic <sup>b</sup>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 0.9A		1.5	1.9	nC
Gate-Source Charge	Q <sub>gs</sub>			0.25		
Gate-Drain Charge	Q <sub>gd</sub>			0.40		
Gate Resistance	R <sub>g</sub>	f = 1 MHz	2	4	8	Ω
Switching						
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 10 V, R <sub>L</sub> = 2.78 Ω I <sub>D</sub> ≅ 0.9 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω		8	15	ns
Rise Time	t <sub>r</sub>			7	15	
Turn-Off Delay Time	t <sub>d(off)</sub>			30	45	
Fall Time	t <sub>f</sub>			7	15	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 0.9 A, dI/dt = 100 A/μs		8.5	15	nC
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			2	4	

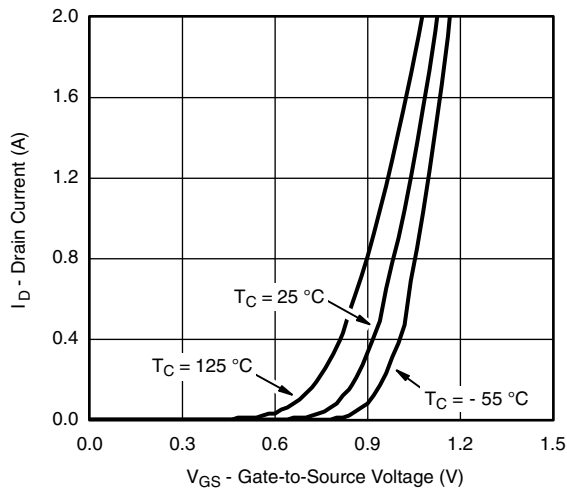
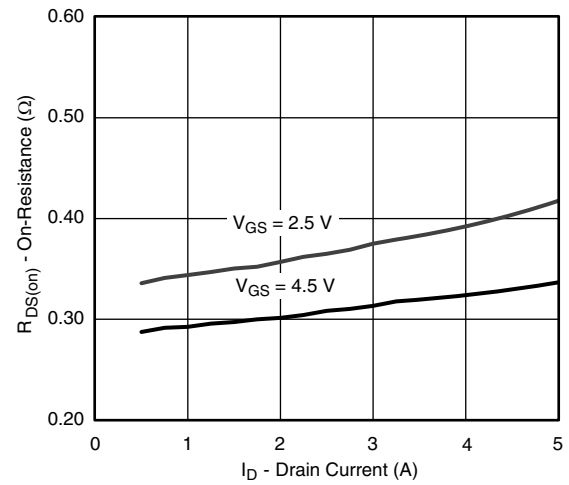
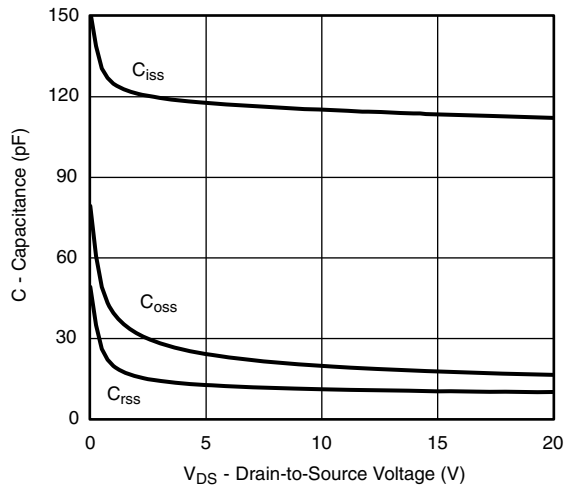
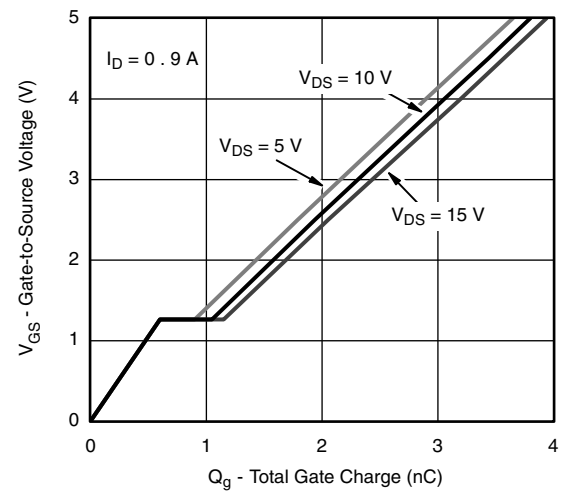
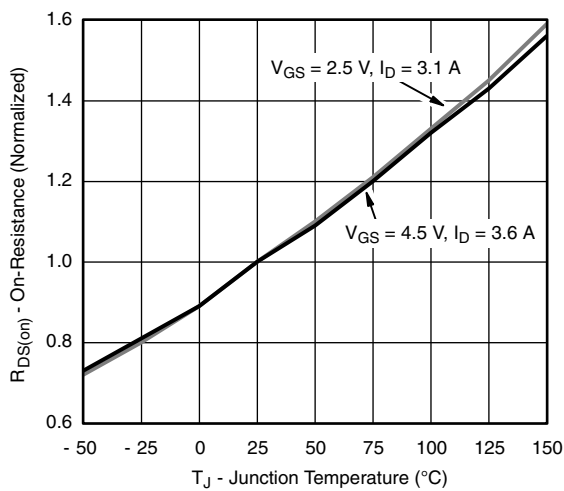
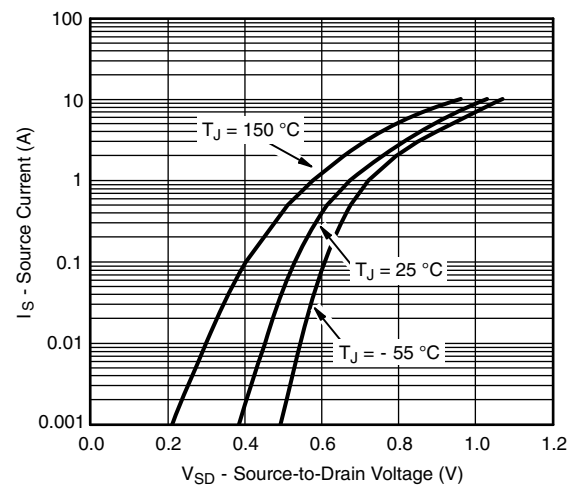
Notes:

a. Pulse test: Pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

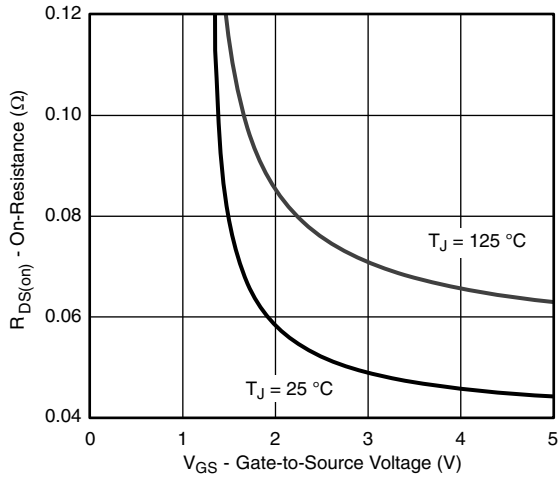
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

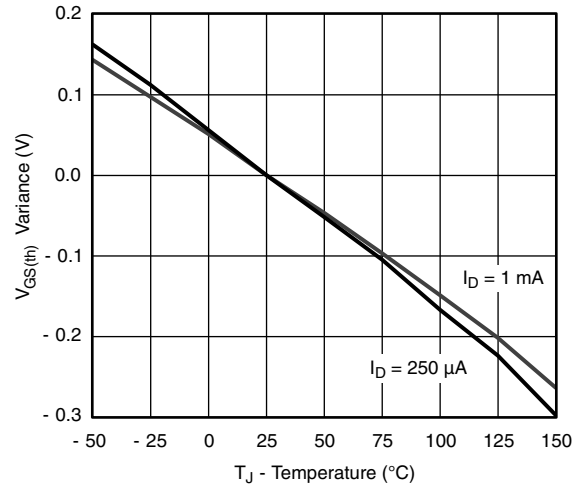
**TYPICAL CHARACTERISTICS** ( $25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

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**Transfer Characteristics**

**On-Resistance vs. Drain Current**

**Capacitance**

**Gate Charge**

**On-Resistance vs. Junction Temperature**

**Source-Drain Diode Forward Voltage**

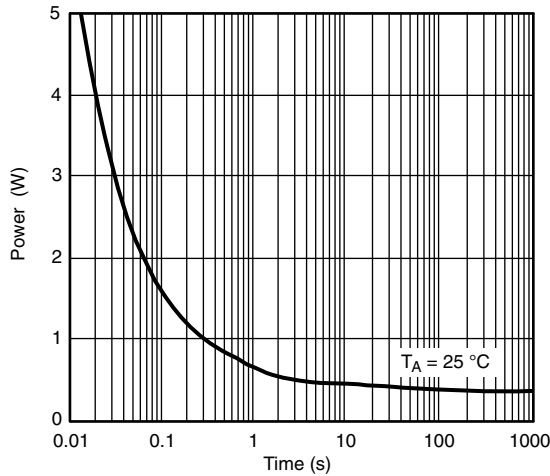
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



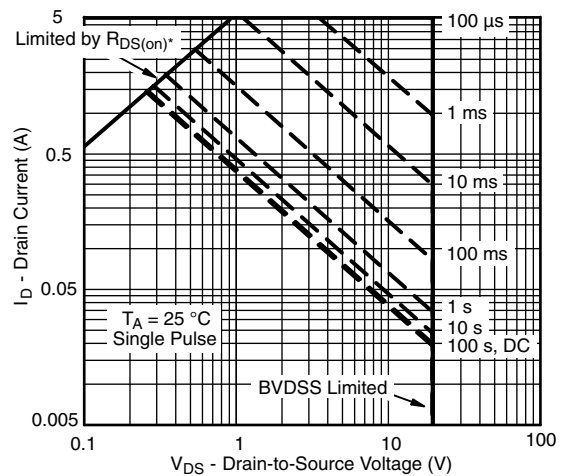
**On-Resistance vs. Gate-to-Source Voltage**



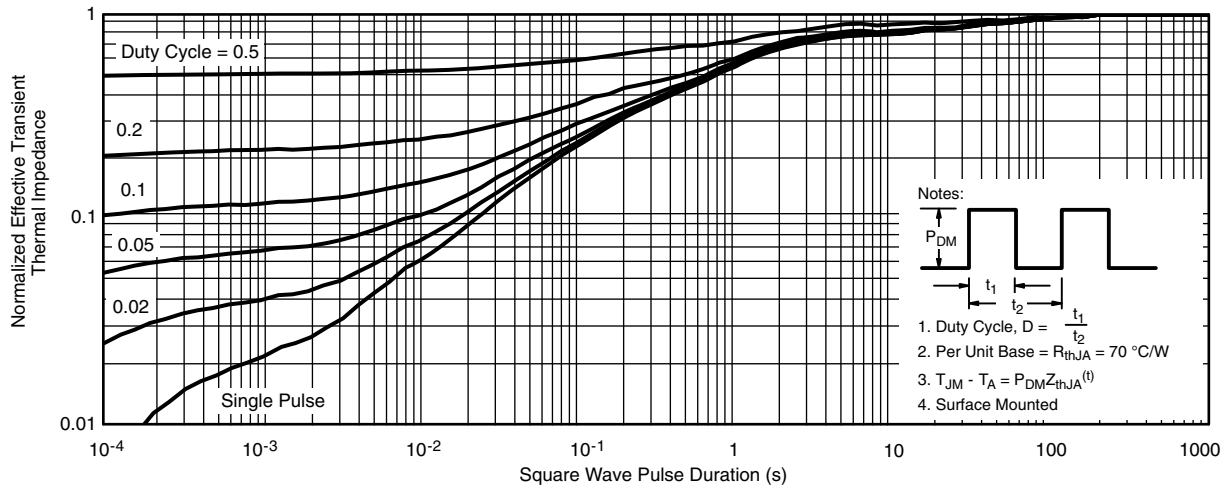
**Threshold Voltage**



**Single Pulse Power**



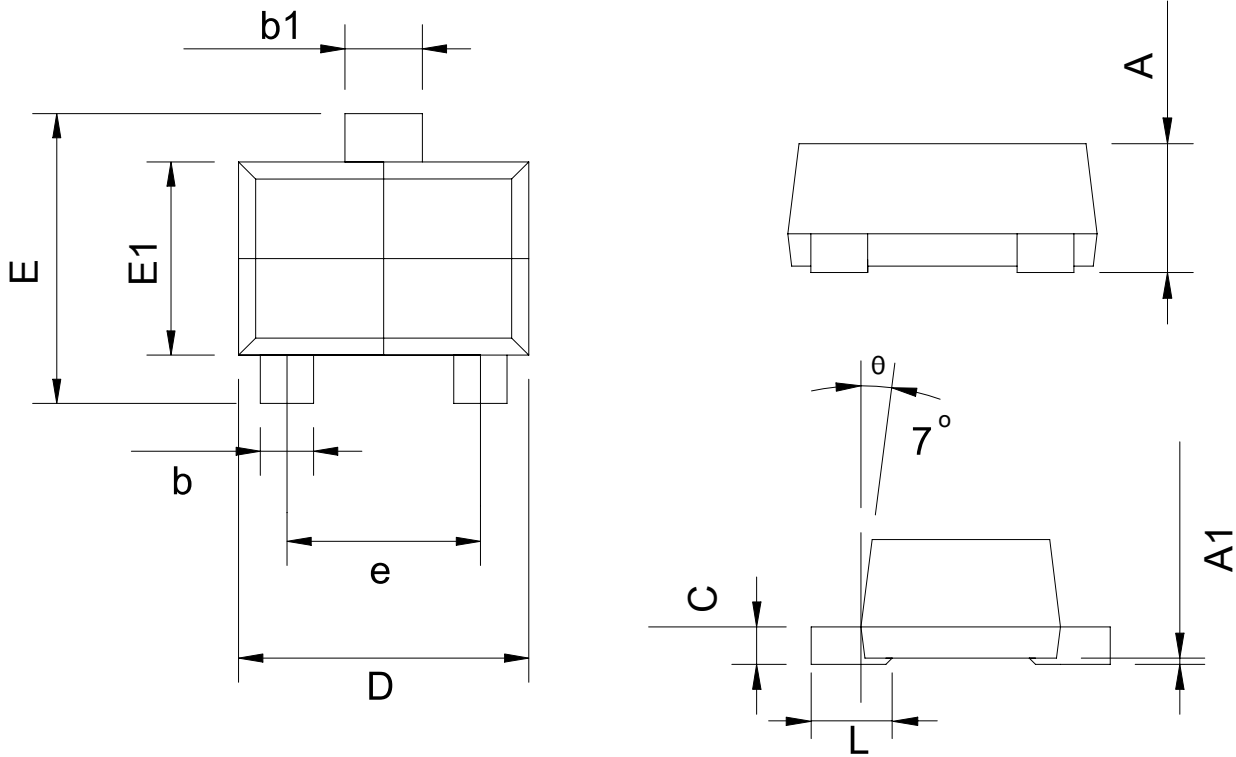
\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified  
**Safe Operating Area, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Ambient**

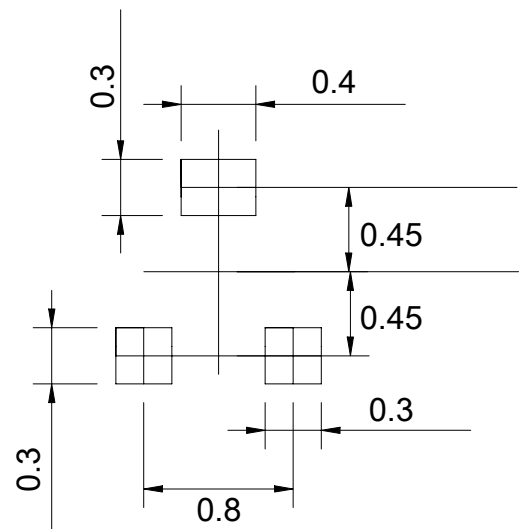
- Notes:
1. Duty Cycle,  $D = \frac{t_1}{t_2}$
  2. Per Unit Base =  $R_{thJA} = 70^\circ\text{C/W}$
  3.  $T_{JM} - T_A = P_{DM}Z_{thJA}^{(t)}$
  4. Surface Mounted

## SOT-723: 3 Leads



SYMBOL	SOT-723			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	-	0.500	-	0.020
A1	0.000	0.050	0.000	0.002
b	0.170	0.270	0.007	0.011
b1	0.270	0.370	0.011	0.015
c	-	0.150	-	0.006
D	1.150	1.250	0.045	0.049
E	1.150	1.250	0.045	0.049
E1	0.750	0.850	0.030	0.033
e	0.800 TYP.		0.031 TYP.	
L	0.32 BSC		0.013 BSC	
-	° REF.		° REF.	

### RECOMMENDED LAND PATTERN



UNIT: mm

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